

B2 end

22. (Amended) The semiconductor device according to claim 20, wherein a thickness of the TaN film is 40 nm or more.

**REMARKS**


In this Supplemental Amendment, Applicants have amended claims 14, 15, 21, and 22 to correct typographical errors inadvertently made in the Amendment filed April 22, 2002. Applicants submit these amendments are not made for reasons related to patentability. In accordance with the requirements of 37 C.F.R. § 1.121(c)(1), Applicants provide a marked-up version of the amendments to the claims in an attached Appendix designated "Version of Claims with Markings to Show Changes Made." Claims 1, 2, and 13 – 22 remain pending.

Please grant any extensions of time under 37 C.F.R. § 1.136 required in entering this response. If there are any fees due under 37 C.F.R. § 1.16 or 1.17, which are not enclosed, including any fees required for an extension of time under 37 C.F.R. § 1.136, please charge such fees to our deposit account 06-0916.

Respectfully submitted,

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